Scott T Dunham

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Nonvolatile Electrically Reconfigurable Integrated Photonic Switch Enabled by a Silicon PIN Diode Heater. Advanced Materials, 2020, 32, e2001218.	21.0	152
2	Variation of Band Gap and Lattice Parameters of βâ^'(Al _{<i>x</i>} Ga _{1â^'<i>x</i>}) ₂ O ₃ Powder Produced by Solution Combustion Synthesis. Journal of the American Ceramic Society, 2016, 99, 2467-2473.	3.8	87
3	Modeling Electrical Switching of Nonvolatile Phase-Change Integrated Nanophotonic Structures with Graphene Heaters. ACS Applied Materials & amp; Interfaces, 2020, 12, 21827-21836.	8.0	78
4	Simulation of grain boundary effects on electronic transport in metals, and detailed causes of scattering. Physica Status Solidi (B): Basic Research, 2010, 247, 1791-1796.	1.5	55
5	Spinodal Decomposition During Anion Exchange in Colloidal Mn ²⁺ -Doped CsPbX ₃ (X = Cl, Br) Perovskite Nanocrystals. Chemistry of Materials, 2019, 31, 7711-7722.	6.7	36
6	Kinetics of Isovalent (Cd ²⁺) and Aliovalent (In ³⁺) Cation Exchange in Cd _{1–<i>x</i>} Mn _{<i>x</i>} Se Nanocrystals. Journal of the American Chemical Society, 2016, 138, 12885-12893.	13.7	30
7	Calculation of Cu/Ta interface electron transmission and effect on conductivity in nanoscale interconnect technology. Applied Physics Letters, 2009, 95, .	3.3	26
8	Stress effects on impurity solubility in crystalline materials: A general model and density-functional calculations for dopants in silicon. Physical Review B, 2009, 79, .	3.2	26
9	Phosphorus vacancy cluster model for phosphorus diffusion gettering of metals in Si. Journal of Applied Physics, 2014, 115, 054906.	2.5	24
10	A simple continuum model for boron clustering based on atomistic calculations. Journal of Applied Physics, 2001, 89, 3650-3655.	2.5	23
11	Dependence of resistivity on surface profile in nanoscale metal films and wires. Journal of Applied Physics, 2008, 103, .	2.5	23
12	Alignment of the diamond nitrogen vacancy center by strain engineering. Applied Physics Letters, 2014, 105, .	3.3	22
13	Universal machine learning framework for defect predictions in zinc blende semiconductors. Patterns, 2022, 3, 100450.	5.9	22
14	Window into NV center kinetics via repeated annealing and spatial tracking of thousands of individual NV centers. Physical Review Materials, 2020, 4, .	2.4	21
15	A model for phosphosilicate glass deposition via POCl3 for control of phosphorus dose in Si. Journal of Applied Physics, 2012, 112, 124912.	2.5	18
16	Calculation of Defect Concentrations and Phase Stability in Cu\$_2\$ ZnSnS\$_4\$ and Cu\$_2\$ ZnSnSe\$_4\$ From Stoichiometry. IEEE Journal of Photovoltaics, 2015, 5, 1188-1196.	2.5	17
17	Modeling of vacancy cluster formation in ion implanted silicon. Journal of Applied Physics, 2001, 89, 4758-4765.	2.5	15
18	First principles calculations of dopant solubility based on strain compensation and direct binding between dopants and group IV impurities. Journal of Vacuum Science & Technology B, 2006, 24, 700.	1.3	12

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19	Combined three-dimensional electromagnetic and device modeling of surface plasmon-enhanced organic solar cells incorporating low aspect ratio silver nanoprisms. Applied Physics Letters, 2013, 103, 183303.	3.3	12
20	The Impact of Charged Grain Boundaries on CdTe Solar Cell: EBIC Measurements Not Predictive of Device Performance. IEEE Journal of Photovoltaics, 2017, 7, 329-334.	2.5	12
21	Ab-initio Calculations to Model Anomalous Fluorine Behavior. Materials Research Society Symposia Proceedings, 2002, 717, 1.	0.1	11
22	Charge carrier induced lattice strain and stress effects on As activation in Si. Applied Physics Letters, 2008, 93, .	3.3	10
23	Design of Anodic Aluminum Oxide Rear Surface Plasmonic Heterostructures for Light Trapping in Thin Silicon Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 1212-1219.	2.5	10
24	Accurate modeling of copper precipitation kinetics including Fermi level dependence. Applied Physics Letters, 2006, 89, 182106.	3.3	9
25	A combined model for {311} defect and dislocation loop evolution: Analytical formulation of kinetic precipitation model. Journal of Applied Physics, 2002, 91, 2883-2889.	2.5	8
26	Calculation of dopant segregation ratios at semiconductor interfaces. Physical Review B, 2008, 78, .	3.2	8
27	Analyzing emitter dopant inhomogeneities at textured Si surfaces by using 3D process and device simulations in combination with SEM imaging. , 2012, , .		8
28	Kinetic lattice Monte Carlo simulations of interdiffusion in strained silicon germanium alloys. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C1G18-C1G23.	1.2	6
29	Modeling Fermi Level Effects in Atomistic Simulations. Materials Research Society Symposia Proceedings, 2002, 717, 1.	0.1	5
30	Correlation factors for interstitial-mediated self-diffusion in the diamond lattice: Kinetic lattice Monte Carlo approach. Physical Review B, 2011, 83, .	3.2	5
31	Defects in Na-, K-, and Cd-Doped CuInSe\$_2\$: Canonical Thermodynamics Based on Ab Initio Calculations. IEEE Journal of Photovoltaics, 2017, 7, 1143-1152.	2.5	5
32	Modeling of Defect Evolution and TED under Stress based on DFT Calculations. , 2006, , .		3
33	Calculations of codoping effects between combinations of donors (P/As/Sb) and acceptors (B/Ga/In) in Si. Journal of Applied Physics, 2007, 102, 123709.	2.5	3
34	Coupled modeling of evolution of impurity/defect distribution and cell performance. , 2012, , .		3
35	Molecular dynamics modeling of solid phase epitaxial regrowth. Journal of Applied Physics, 2012, 111, 114504.	2.5	3
36	Ab Initio Study of Carbon Impurities in Cu\$_2\$ ZnSnS\$_4\$. IEEE Journal of Photovoltaics, 2016, 6, 562-570.	2.5	3

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37	Understanding and Modeling Ramp Rate Effects on Shallow Junction Formation. Materials Research Society Symposia Proceedings, 2000, 610, 481.	0.1	2
38	3D Optical and device simulation of surface plasmonic effects on organic solar cells using silver nano prisms. , 2011, , .		2
39	End-to-end predictive modeling of silicon solar cell performance: From process recipe to device simulation. , 2011, , .		2
40	First-principles calculations of Na and K impurities in CuInSe <inf>2</inf> and their effect on Cd incorporation. , 2016, , .		2
41	Atomistic models of Cu diffusion in CulnSe2 under variations in composition. Journal of Applied Physics, 2018, 123, 115116.	2.5	2
42	Modeling of Annealing of High Concentration Arsenic Profiles. Materials Research Society Symposia Proceedings, 2001, 669, 1.	0.1	1
43	Atomistic Simulations of Effect of Coulombic Interactions on Carrier Fluctuations in Doped Silicon. Materials Research Society Symposia Proceedings, 2003, 765, 1.	0.1	1
44	Predictive models for co-doping effects between combinations of donors (P/As/Sb) and acceptors (B/Ga/In). , 2006, , .		1
45	Atomistic modeling of dopant diffusion and segregation in strained SiGeC. , 2008, , .		1
46	Multiscale modeling of nanoscale device fabrication. , 2010, , .		1
47	Enhanced EBIC response but degraded solar cell performance for CdTe grain boundaries. , 2016, , .		1
48	Monte Carlo modeling of phase separation in Culn <inf>x</inf> Ga <inf>1â^'x</inf> Se <inf>2</inf> . , 2016, ,		1
49	Understanding copper diffusion in CuInSe2 with first-principles based atomistic and continuum models. Journal of Applied Physics, 2021, 130, .	2.5	1
50	Stress Effects on As Activation in Si. Materials Research Society Symposia Proceedings, 2007, 994, 1.	0.1	0
51	A comparison of optical modulator structures using a matrix simulation approach. Optical and Quantum Electronics, 2008, 40, 431-437.	3.3	0
52	Ab Initio Calculations of Crystalline and Amorphous In2Se3 Compounds for Chalcogenide Phase Change Memory. Materials Research Society Symposia Proceedings, 2010, 1251, 34.	0.1	0
53	Optical and Electrical Modeling of Polymer Thin-film Photovoltaics. Materials Research Society Symposia Proceedings, 2010, 1270, 1.	0.1	0
54	Formation energies of carbon related defects in Cu <inf>2</inf> ZnSnS <inf>4</inf> . , 2014, , .		0

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55	Calculation of defect concentrations in Cu <inf>2</inf> ZnSnS <inf>4</inf> from stoichiometry. , 2014, , .		0
56	Interaction of O _{2i} Dimers with Ga in Si and Implications for a Comprehensive Model of Light- Induced Degradation. , 2017, , .		0
57	Reduced photothermal heating in diamonds enriched with H3 point defects. Journal of Applied Physics, 2022, 131, 234401.	2.5	0